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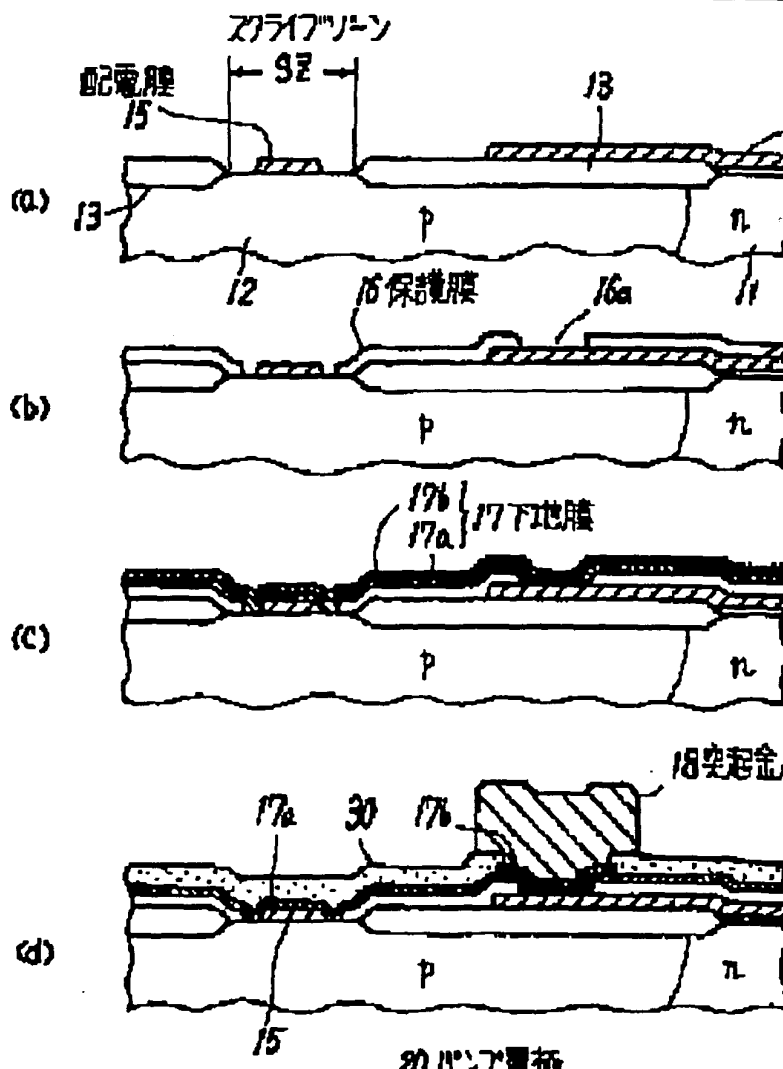
(74) Representative:

(54) ELECTROLYTIC PLATING FOR BUMP ELECTRODE FOR INTEGRATED CIRCUIT DEVICE

(57) Abstract:

PURPOSE: To easily eliminate the irregularity of height of the projecting metal for bump electrode, which is subject to electrolytic plating growth, in an integrated circuit in which the chips buried in a wafer has not been separated yet.

CONSTITUTION: A distribution film 15 of high conductive metal is provided in a grid pattern within a mutual scribe zone SZ of chip area in a wafer 10, and after each chip area of the wafer is covered with a protective film 16, the window is opened at the position to provide a bump electrode 20 projectingly. Then a metallic and thin base film 17 is adhered on the wafer surface in a manner to connect the film 15 and the distribution film 14 in the window of film 16, and a projecting metal 18 is grown on the connected position to the film 14 through an electrolytic plating while using the film 17 as a plating electrode.



film 17 as a plating electrode.

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